

## EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	2392	salicide and CMOS	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/22 15:44
S2	1985	S1 and silicide	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/31 15:31
S3	543	S2 and STI	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/31 15:34
S4	474	leakage with STI	US-PGPUB; USPAT	OR	ON	2005/08/31 15:35
S5	205	S4 and silicide	US-PGPUB; USPAT	OR	ON	2005/08/31 17:11
S6	2035	438/630,645,651,655,663,664,682. ccls.	US-PGPUB; USPAT	OR	ON	2007/09/01 17:11
S7	72	S6 and STI and leakage	US-PGPUB; USPAT	OR	ON	2005/08/31 17:21
S8	826	438/630,645,651,655,663,664,682. ccls. and ((work with function) or work function or worf\$function)	US-PGPUB; USPAT	OR	ON	2005/09/01 15:14
S9	77	438/630,645,651,655,663,664,682. ccls. and ((work with function) or workfunction or worf\$function)	US-PGPUB; USPAT	OR	ON	2005/09/01 15:14
S10	20037	(CMOS or MOSFET) and (silicide or salicide)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/22 15:46
S11	7035	S10 and (oxide with (film or layer)) and anneal\$3 and ((remov\$3 or etch\$3) with oxide) and silicide	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/22 15:47

## EAST Search History

S12	1143	S11 and (first with anneal\$3) and (second with anneal\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/22 15:48
S13	90	spike with rapid with thermal with anneal\$3	USPAT	OR	ON	2007/04/24 11:53
S14	7	S13 and (zero with second)	USPAT	OR	ON	2007/04/24 11:53
S16	964	S15 and (oxide with (film or layer)) and ((rapid with thermal) or RTA)	US-PGPUB; USPAT	OR	ON	2007/09/01 17:14
S17	20256	selective\$3 with (remov\$3 or etch\$3) with oxide	US-PGPUB; USPAT	OR	ON	2007/09/01 17:15
S18	205	S16 and (selective\$3 with (remov\$3 or etch\$3) with oxide)	US-PGPUB; USPAT	OR	ON	2007/09/01 17:15
S19	2037	438/630,663,664,682.ccls. or 257/E21.199.ccls.	US-PGPUB; USPAT	OR	ON	2007/09/01 18:05
S20	20	((oxide with (film or layer)) and (substrate or wafer) and (MOS or FET or MOSFET or transistor) and ((rapid with thermal) or RTA) and (selective\$3 with (remov\$3 or etch\$3)) and metal\$4 and silicide). CLM.	US-PGPUB	OR	ON	2007/09/01 18:10
S21	6	((oxide with (film or layer)) and (substrate or wafer) and (MOS or FET or MOSFET or transistor) and ((rapid with thermal) or RTA) and (selective\$3 with (remov\$3 or etch\$3) with oxide) and metal\$4 and silicide).CLM.	US-PGPUB	OR	ON	2007/09/01 18:10